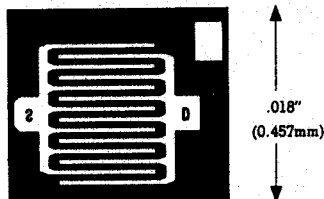


CHIP NUMBER
FN7.1



← .023"
 (0.584mm) →

Die Size: 18 x 23 (mils)
 0.457 x .0584(mm)
 3 x 3 (mils)
 Pad Size: 0.076 x 0.076(mm)
 GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

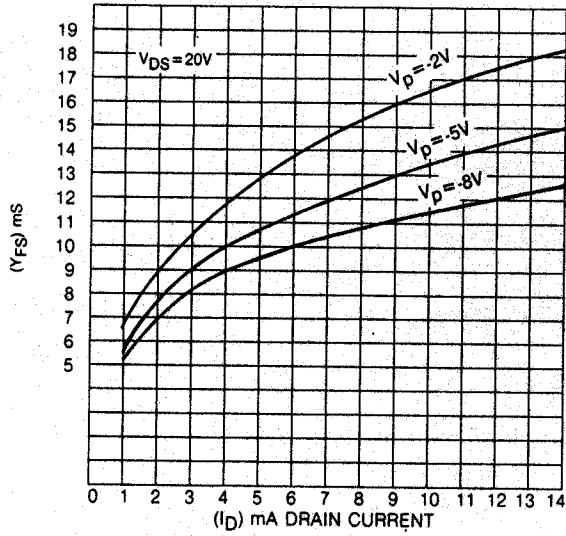
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-30	-50	-70	V	V _{DS} = 0, I _G = 1μA
I _{DSS}	5.0	60	150	mA	V _{DS} = 20V, V _{GS} = 0
g _{fs}		8		mmho	V _{DS} = 20V, I _D = 2mA
I _{GSS}		-20	-200	pA	V _{GS} = -20V, V _{DS} = 0
r _{DS}	20	40	100	Ω	V _{DS} = 100mV, V _{GS} = 0
V _{GS(off)}	-0.5	-4.5	-10	V	V _{DS} = 20V, I _D = 1nA
C _{rss}	3.0	3.5	4.0	pF	V _{DS} = 15V, I _D = 5mA, f = 1MHz
C _{iss}	10	12	16	pF	V _{DS} = 15V, I _D = 5mA, f = 1MHz
ē _n		7		nV/√Hz	V _{DS} = 15V, I _D = 5mA, f = 1KHz

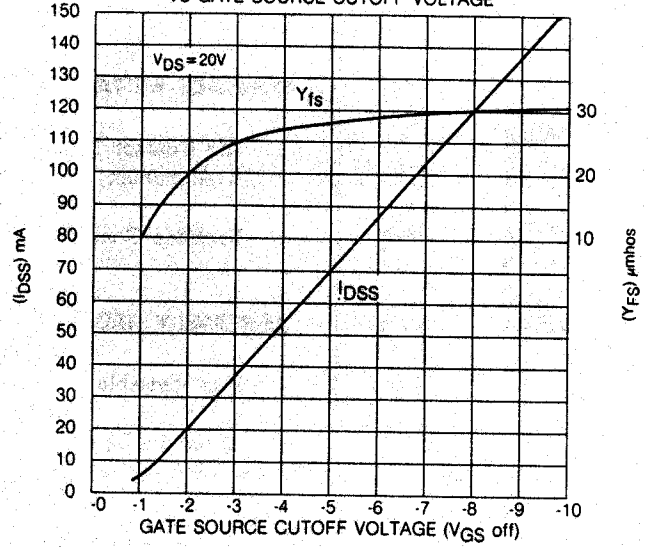
TYPICAL DEVICE TYPES: 2N4091 - 2N4093, 2N4391 - 2N4393, 2N4856 - 2N4861, KK4391 - KK4393

CHIP TYPE FN7.1

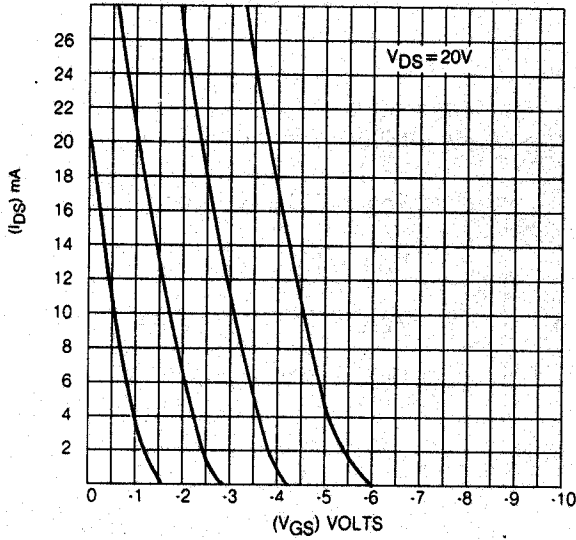
FORWARD TRANSADMITTANCE



SHORT CIRCUIT FORWARD TRANSADMITTANCE VS GATE SOURCE CUTOFF VOLTAGE



TRANSFER CHARACTERISTICS



COMMON SOURCE DRAIN CHARACTERISTICS

